
ISL72027ASEH**3.3V Radiation Tolerant CAN Transceivers with Listen Mode and Split Termination Output**FN8862
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The Intersil [ISL72027ASEH](#) is a 3.3V, radiation tolerant CAN transceiver that is compatible with the ISO11898-2 standard for applications calling for Controller Area Network (CAN) serial communication in satellites and aerospace communications and telemetry data processing in harsh industrial environments.

This device can transmit and receive at bus speeds up to 5Mbps. It can drive a 40m cable at 1Mbps according to the ISO11898-2 specification. The device is designed to operate across a common-mode range of -7V to +12V, with a maximum of 120 nodes. It has three discrete selectable driver rise/fall time options, a Listen mode feature, and a split termination output.

The receiver (Rx) inputs feature a “full fail-safe” design, which ensures a logic high Rx output if the Rx inputs are floating, shorted, or terminated but undriven.

The ISL72027ASEH is available in an 8 Ld hermetic ceramic flatpack and die form that operate across the temperature range of -55°C to +125°C. The logic inputs are tolerant with 5V systems.

Other CAN transceivers available are the [ISL72026ASEH](#) and [ISL72028ASEH](#). For a list of differences between these devices, refer to [Table 1 on page 4](#).

Applications

- Satellites and aerospace communications
- Telemetry data processing and high-end industrial

Related Literature

- For a full list of related documents, visit our website
 - [ISL72027ASEH](#) product page

Features

- Electrically screened to SMD [5962-15228](#)
- ESD protection on all pins: 4kV HBM
- Compatible with ISO11898-2
- Operating supply range: 3.0V to 3.6V
- Bus pin fault protection to ±20V
- Undervoltage lockout
- Cold spare: powered down devices/nodes do not affect active devices operating in parallel
- Three selectable driver rise and fall times:
 - Fast speed (RS = 0V) - edges and propagation delays optimized for a data rate of 1Mbps
 - Medium speed (RS = 10kΩ) - edges and propagation delays optimized for a data rate of 500kbps
 - Slow Speed (RS = 50kΩ) - edges and propagation delays optimized for a data rate of 250kbps
- Glitch free bus I/O during power-up and power-down
- Full fail-safe (open, short, terminated/undriven) receiver
- Hi-Z input allows for 120 nodes on the bus
- High data rates: up to 5Mbps
- Quiescent supply current: 7mA (maximum)
- Listen mode supply current: 2mA (maximum)
- -7V to +12V common-mode input voltage range
- 5V tolerant logic inputs
- Thermal shutdown
- Acceptance tested to 75krad(Si) (LDR) wafer-by-wafer
- Radiation tolerance
 - SEL/B immune to LET_{TH}: 86.4MeV•cm²/mg
 - Low dose rate (0.01rad(Si)/s): 75krad(Si)

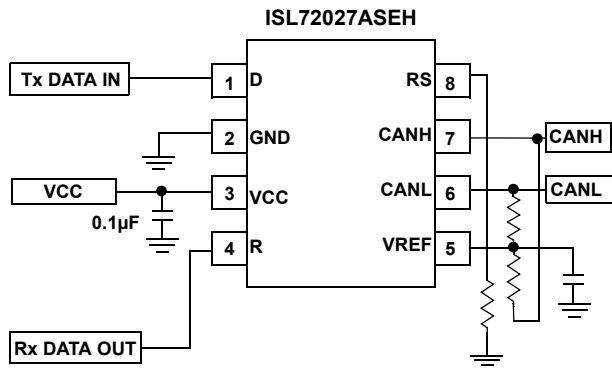


Figure 1. Typical Application

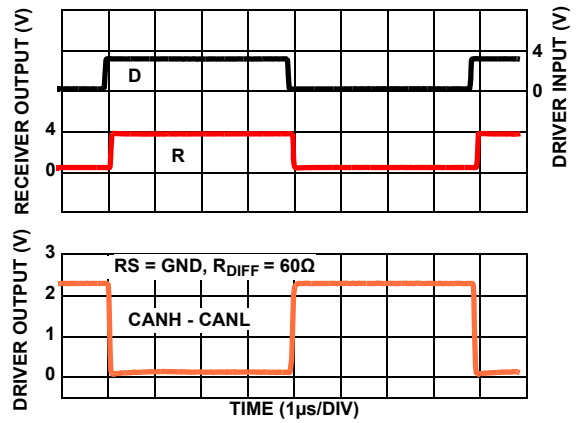


Figure 2. Fast Driver and Receiver Waveforms

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1. Overview

1.1 Ordering Information

| Ordering/SMD Number (Note 1) | Part Number (Note 2) | Temp Range (°C) | Package (RoHS Compliant) | Pkg. Dwg. # |
|----------------------------------------------|------------------------------------------------|------------------|--------------------------|-------------|
| 5962L1522808VXC | ISL72027ASEHVF | -55 to +125 | 8 Ld Ceramic Flatpack | K8.A |
| N/A | ISL72027ASEHF/PROTO, (Note 3) | -55 to +125 | 8 Ld Ceramic Flatpack | K8.A |
| 5962L1522808V9A | ISL72027ASEHVX | -55 to +125 | Die | |
| N/A | ISL72027ASEHX/SAMPLE, (Note 3) | -55 to +125 | Die | |
| N/A | ISL72027ASEHEVAL1Z, (Note 4) | Evaluation Board | | |

Notes:

- Specifications for Radiation Tolerant QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed in the Ordering Information must be used when ordering.
- These Intersil Pb-free Hermetic packaged products employ 100% Au plate -e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.
- The /PROTO and /SAMPLE are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity. These parts are intended for engineering evaluation purposes only. The /PROTO parts meet the electrical limits and conditions over-temperature specified in the DLA SMD and are in the same form and fit as the qualified device. The /SAMPLE die is capable of meeting the electrical limits and conditions specified in the DLA SMD at +25°C only. The /SAMPLE is a die and does not receive 100% screening over-temperature to the DLA SMD electrical limits. These part types do not come with a Certificate of Conformance because there is no radiation assurance testing and they are not DLA qualified devices.
- Evaluation boards utilize the /PROTO parts and /PROTO parts are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity.

Table 1. ISL7202xxSEH Product Family Feature Table

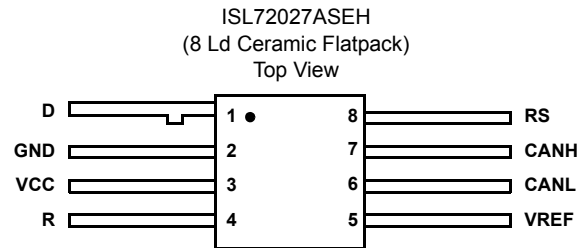
| Specification | ISL72026ASEH | ISL72027ASEH | ISL72028ASEH |
|-------------------------------|-----------------|-----------------|-----------------|
| Loopback Feature | Yes | No | No |
| VREF Output | No | Yes | Yes |
| Listen Mode | Yes | Yes | No |
| Shutdown Mode | No | No | Yes |
| VTHRLM | 900mV (maximum) | 900mV (maximum) | N/A |
| VTHFLM | 325mV (minimum) | 325mV (minimum) | N/A |
| VHYSLM | 40mV (minimum) | 40mV (minimum) | N/A |
| Supply Current, Listen Mode | 2mA (maximum) | 2mA (maximum) | N/A |
| Supply Current, Shutdown Mode | N/A | N/A | 50µA (maximum) |
| VREF Leakage Current | N/A | ±25µA (maximum) | ±25µA (maximum) |

Note:N/A = Not Applicable

Table 2. Product Family Comparison for Optimal Data Rate and Total Dose Radiation Testing

| Specification | ISL7202xSEH | ISL7202xASEH | ISL7202xBSEH | ISL7202xCSEH |
|------------------------------------------|-------------|--------------|--------------|--------------|
| Data Rate: RS = 0V | 1Mbps | 1Mbps | 1Mbps | 1Mbps |
| Data Rate: RS = 10kΩ | 250kbps | 500kbps | 250kbps | 500kbps |
| Data Rate: RS = 50kΩ | 125kbps | 250kbps | 125kbps | 250kbps |
| High Dose Rate (HDR) 100krad(Si) Testing | No | No | Yes | Yes |
| Low Dose Rate (LDR) 75krad(Si) Testing | Yes | Yes | Yes | Yes |

1.2 Pin Configuration



Note: The package lid is tied to ground.

1.3 Pin Descriptions

| Pin Number | Pin Name | Function |
|------------|----------|---------------------------------------------------------------------------------------------------------------------------------------------|
| 1 | D | CAN driver digital input. A LOW bus state is Dominant and a HIGH bus state is Recessive. Internally tied HIGH. |
| 2 | GND | Ground connection. |
| 3 | VCC | System power supply input (3.0V to 3.6V). The typical voltage for the device is 3.3V. |
| 4 | R | CAN data receiver output. A LOW bus state is Dominant and a HIGH bus state is Recessive. |
| 5 | VREF | VCC/2 reference output for split mode termination. |
| 6 | CANL | CAN bus line for low level output. |
| 7 | CANH | CAN bus line for high level output. |
| 8 | RS | A resistor to GND from this pin controls the rise and fall time of the CAN output waveform. Drive RS HIGH to put the device in Listen mode. |

1.4 Equivalent Input and Output Schematic Diagrams

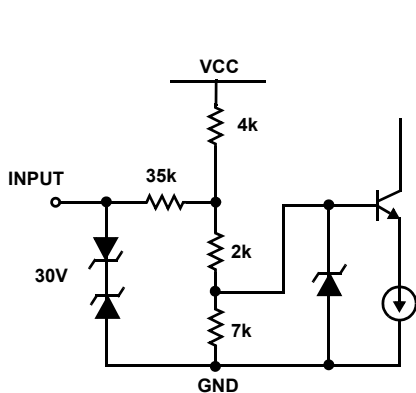


Figure 3. CANH and CANL Inputs

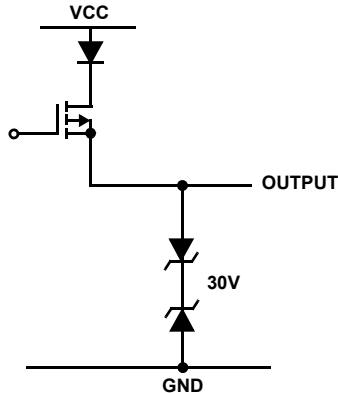


Figure 4. CANH Output

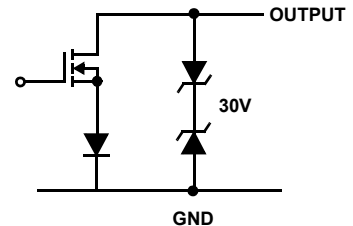


Figure 5. CANL Output

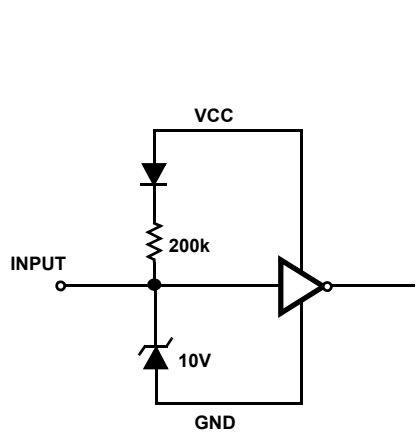


Figure 6. D Input

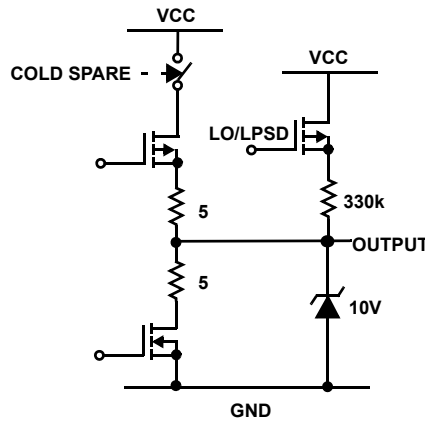


Figure 7. R Output

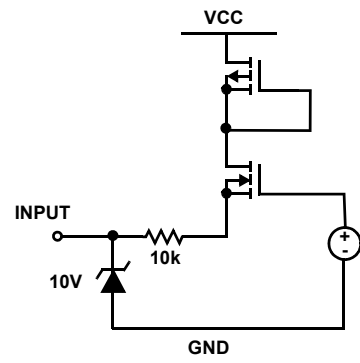


Figure 8. RS Input

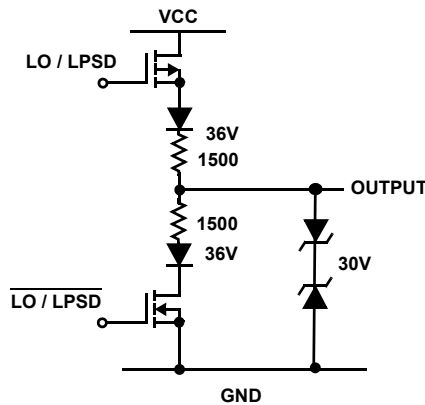


Figure 9. VREF

2. Specifications

2.1 Absolute Maximum Ratings

| Parameter | Minimum | Maximum | Unit |
|----------------------------------------------------|--------------|---------|-------------|
| VCC to GND with/without Ion Beam | -0.3 | 5.5 | V |
| CANH, CANL, VREF Under Ion Beam | | ±20 | V |
| CANH, CANL, VREF | | ±20 | V |
| I/O Voltages D, R, RS | -0.5 | 7 | V |
| Receiver Output Current | -10 | 10 | mA |
| Output Short-Circuit Duration | Continuous | | |
| ESD Rating | Value | | Unit |
| Human Body Model (Tested per MIL-STD-883 TM3015.7) | | | |
| CANH, CANL Bus Pins | | 4 | kV |
| All Other Pins | | 4 | kV |
| Charged Device Model (Tested per JS-002-2014) | | 750 | V |
| Machine Model (Tested per JESD22-A115C) | | 200 | V |

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

2.2 Thermal Information

| Thermal Resistance (Typical) | θ_{JA} (°C/W) | θ_{JC} (°C/W) |
|------------------------------------------------|----------------------|----------------------|
| 8 Ld FP Package (Notes 5, 6) | 39 | 7 |

Notes:

- θ_{JA} is measured with the component mounted on a high-effective thermal conductivity test board (two buried 1oz copper planes) with "direct attach" features package base mounted to PCB thermal land with a 10 mil gap fill material having a thermal conductivity of 1W/m-K. Refer to [TB379](#).
- For θ_{JC} , the "case temp" location is the center of the package underside.

| Parameter | Minimum | Maximum | Unit |
|------------------------------|---------|---------|------|
| Maximum Junction Temperature | | +150 | °C |
| Storage Temperature Range | -65 | +150 | °C |

2.3 Recommended Operating Conditions

| Parameter | Minimum | Maximum | Unit |
|---------------------------------------------------------------------|---------|---------|------|
| Temperature Range | -55 | +125 | °C |
| V _{CC} Supply Voltage | 3 | 3.6 | V |
| Voltage on CAN I/O | -7 | 12 | V |
| V _{IH} D Logic Pin | 2 | 5.5 | V |
| V _{IL} D Logic Pin | 0 | 0.8 | V |
| I _{OH} Driver (CANH - CANL = 1.5V, V _{CC} = 3.3V) | | -40 | mA |
| I _{OH} Receiver (V _{OH} = 2.4V) | | -4 | mA |
| I _{OL} Driver (CANH - CANL = 1.5V, V _{CC} = 3.3V) | | 40 | mA |
| I _{OL} Receiver (V _{OL} = 0.4V) | | 4 | mA |

2.4 Electrical Specifications

Test Conditions: V_{CC} = 3V to 3.6V; typical values are at T_A = +25°C (Note 9); unless otherwise specified (Note 7). **Boldface limits apply across the operating temperature range, -55°C to +125°C and over a total ionizing dose of 75krad(Si) at +25°C with exposure at a low dose rate of <10mrad(Si)/s.**

| Parameter | Symbol | Test Conditions | Temp (°C) | Min (Note 8) | Typ (Note 9) | Max (Note 8) | Unit | |
|------------------------------------------|----------------------|-----------------------------------------------------------------|-----------------------------|--------------|----------------------------|--------------|-----------------|----|
| Driver Electrical Characteristics | | | | | | | | |
| Dominant Bus Output Voltage | V _{O(DOM)} | D = 0V, CANH, RS = 0V, Figures 10 and 11 | 3V ≤ V _{CC} ≤ 3.6V | Full | 2.25 | 2.85 | V _{CC} | V |
| | | D = 0V, CANL, RS = 0V, Figures 10 and 11 | | Full | 0.10 | 0.65 | 1.25 | V |
| Recessive Bus Output Voltage | V _{O(REC)} | D = 3V, CANH, RS = 0V, 60Ω and no load, Figures 10 and 11 | 3V ≤ V _{CC} ≤ 3.6V | Full | 1.80 | 2.30 | 2.70 | V |
| | | D = 3V, CANL, RS = 0V, 60Ω and no load, Figures 10 and 11 | | Full | 1.80 | 2.30 | 2.80 | V |
| Dominant Output Differential Voltage | V _{OD(DOM)} | D = 0V, RS = 0V, 3V ≤ V _{CC} ≤ 3.6V, Figures 10 and 11 | | Full | 1.5 | 2.2 | 3.0 | V |
| | | D = 0V, RS = 0V, 3V ≤ V _{CC} ≤ 3.6V, Figures 11 and 12 | | Full | 1.2 | 2.1 | 3.0 | V |
| Recessive Output Differential Voltage | V _{OD(REC)} | D = 3V, RS = 0V, 3V ≤ V _{CC} ≤ 3.6V, Figures 10 and 11 | | Full | -120 | 0.2 | 12 | mV |
| | | D = 3V, RS = 0V, 3.0V ≤ V _{CC} ≤ 3.6V, no load | | Full | -500 | -34 | 50 | mV |
| Logic Input High Voltage (D) | V _{IH} | 3V ≤ V _{CC} ≤ 3.6V, (Note 10) | | Full | 2.0 | - | 5.5 | V |
| Logic Input Low Voltage (D) | V _{IL} | 3V ≤ V _{CC} ≤ 3.6V, (Note 10) | | Full | 0 | - | 0.8 | V |
| High Level Input Current (D) | I _{IH} | D = 2V, 3V ≤ V _{CC} ≤ 3.6V | | Full | -30 | -3 | 30 | μA |
| Low Level Input Current (D) | I _{IL} | D = 0.8V, 3V ≤ V _{CC} ≤ 3.6V | | Full | -30 | -7 | 30 | μA |
| RS Input Voltage for Listen Mode | V _{IN(RS)} | 3V ≤ V _{CC} ≤ 3.6V | | Full | 0.75xV_{CC} | 1.90 | 5.5 | V |

Test Conditions: $V_{CC} = 3V$ to $3.6V$; typical values are at $T_A = +25^\circ C$ (Note 9); unless otherwise specified (Note 7). **Boldface limits apply across the operating temperature range, $-55^\circ C$ to $+125^\circ C$ and over a total ionizing dose of $75krad(Si)$ at $+25^\circ C$ with exposure at a low dose rate of $<10mrad(Si)/s$.** (Continued)

| Parameter | Symbol | Test Conditions | Temp (°C) | Min (Note 8) | Typ (Note 9) | Max (Note 8) | Unit |
|-----------------------------------------------|-------------|------------------------------------------------------------------------------|-----------|--------------|--------------|--------------|------|
| Output Short-Circuit Current | I_{OSC} | $V_{CANH} = -7V$, CANL = OPEN, $3V \leq V_{CC} \leq 3.6V$, Figure 23 | Full | -250 | -100 | - | mA |
| | | $V_{CANH} = +12V$, CANL = OPEN, $3V \leq V_{CC} \leq 3.6V$, Figure 23 | Full | - | 0.4 | 1.0 | mA |
| | | $V_{CANL} = -7V$, CANH = OPEN, $3V \leq V_{CC} \leq 3.6V$, Figure 23 | Full | -1.0 | -0.4 | - | mA |
| | | $V_{CANL} = +12V$, CANH = OPEN, $3V \leq V_{CC} \leq 3.6V$, Figure 23 | Full | - | 100 | 250 | mA |
| Thermal Shutdown Temperature | T_{SHDN} | $3V < V_{IN} < 3.6V$ | - | - | 163 | - | °C |
| Thermal Shutdown Hysteresis | T_{HYS} | $3V < V_{IN} < 3.6V$ | - | - | 12 | - | °C |
| Receiver Electrical Characteristics | | | | | | | |
| Input Threshold Voltage (Rising) | V_{THR} | RS = 0V, 10k, 50k, (recessive to dominant), Figure 17 and Table 3 | Full | - | 700 | 900 | mV |
| Input Threshold Voltage (Falling) | V_{THF} | RS = 0V, 10k, 50k, (dominant to recessive), Figure 17 and Table 3 | Full | 500 | 625 | - | mV |
| Input Hysteresis | V_{HYS} | $(V_{THR} - V_{THF})$, RS = 0V, 10k, 50k, Figure 17 and Table 3 | Full | 40 | 80 | - | mV |
| Listen Mode Input Threshold Voltage (Rising) | V_{THRLM} | RS = V_{CC} , (recessive to dominant), Figure 17 | Full | - | 650 | 900 | mV |
| Listen Mode Input Threshold Voltage (Falling) | V_{THFLM} | RS = V_{CC} , (dominant to recessive), Figure 17 | Full | 325 | 550 | - | mV |
| Listen Mode Input Hysteresis | V_{HYSLM} | $(V_{THR} - V_{THF})$, RS = V_{CC} , Figure 17 | Full | 40 | 100 | - | mV |
| Receiver Output High Voltage | V_{OH} | $I_O = -4mA$ | Full | 2.4 | $V_{CC}-0.2$ | - | V |
| Receiver Output Low Voltage | V_{OL} | $I_O = +4mA$ | Full | - | 0.2 | 0.4 | V |
| Input Current for CAN Bus | I_{CAN} | CANH or CANL at 12V, D = 3V, other bus pin at 0V, RS = 0V | Full | - | 470 | 600 | μA |
| | | CANH or CANL at 12V, D = 3V, $V_{CC} = 0V$, other bus pin at 0V, RS = 0V | Full | - | 170 | 275 | μA |
| | | CANH or CANL at -7V, D = 3V, other bus pin at 0V, RS = 0V | Full | -500 | -350 | - | μA |
| | | CANH or CANL at -7V, D = 3V, $V_{CC} = 0V$, other bus pin at 0V, RS = 0V | Full | -175 | -100 | - | μA |
| Input Capacitance (CANH or CANL) | C_{IN} | Input to GND, D = 3V, RS = 0V | 25 | - | 35 | - | pF |
| Differential Input Capacitance | C_{IND} | Input to Input, D = 3V, RS = 0V | 25 | - | 15 | - | pF |
| Input Resistance (CANH or CANL) | R_{IN} | Input to GND, D = 3V, RS = 0V | Full | 20 | 40 | 50 | kΩ |
| Differential Input Resistance | R_{IND} | Input to Input, D = 3V, RS = 0V | Full | 40 | 80 | 100 | kΩ |
| Supply Current | | | | | | | |

Test Conditions: $V_{CC} = 3V$ to $3.6V$; typical values are at $T_A = +25^\circ C$ (Note 9); unless otherwise specified (Note 7). **Boldface limits apply across the operating temperature range, $-55^\circ C$ to $+125^\circ C$ and over a total ionizing dose of $75krad(Si)$ at $+25^\circ C$ with exposure at a low dose rate of $<10mrad(Si)/s$.** (Continued)

| Parameter | Symbol | Test Conditions | Temp (°C) | Min (Note 8) | Typ (Note 9) | Max (Note 8) | Unit |
|--------------------------------------------------------------------------|---------------|----------------------------------------------------------------------------------|-----------|--------------|--------------|--------------|---------|
| Supply Current, Listen Mode | $I_{CC(L)}$ | $RS = D = V_{CC}, 3V \leq V_{CC} \leq 3.6V$ | Full | - | 1 | 2 | mA |
| Supply Current, Dominant | $I_{CC(DOM)}$ | $D = RS = 0V$, no load, $3V \leq V_{CC} \leq 3.6V$ | Full | - | 5 | 7 | mA |
| Supply Current, Recessive | $I_{CC(REC)}$ | $D = V_{CC}, RS = 0V$, no load, $3V \leq V_{CC} \leq 3.6V$ | Full | - | 2.6 | 5.0 | mA |
| Cold Sparing Bus Current | | | | | | | |
| CANH Leakage Current | $I_{L(CANH)}$ | $V_{CC} = 0.2V$, CANH = $-7V$ or $12V$, CANL = float, $D = V_{CC}$, $RS = 0V$ | Full | -25 | -4 | 25 | μA |
| CANL Leakage Current | $I_{L(CANL)}$ | $V_{CC} = 0.2V$, CANL = $-7V$ or $12V$, CANH = float, $D = V_{CC}$, $RS = 0V$ | Full | -25 | -4 | 25 | μA |
| V_{REF} Leakage Current | $I_{L(VREF)}$ | $V_{CC} = 0.2V$, $V_{REF} = -7V$ or $12V$, $D = V_{CC}$ | Full | -25 | 0.01 | 25 | μA |
| Driver Switching Characteristics | | | | | | | |
| Propagation Delay LOW to HIGH | t_{PDLH1} | $RS = 0V$, Figure 14 | Full | - | 90 | 160 | ns |
| Propagation Delay LOW to HIGH | t_{PDLH2} | $RS = 10k\Omega$, Figure 14 | Full | - | 350 | 550 | ns |
| Propagation Delay LOW to HIGH | t_{PDLH3} | $RS = 50k\Omega$, Figure 14 | Full | - | 475 | 800 | ns |
| Propagation Delay HIGH to LOW | t_{PDHL1} | $RS = 0V$, Figure 14 | Full | - | 115 | 180 | ns |
| Propagation Delay HIGH to LOW | t_{PDHL2} | $RS = 10k\Omega$, Figure 14 | Full | - | 410 | 600 | ns |
| Propagation Delay HIGH to LOW | t_{PDHL3} | $RS = 50k\Omega$, Figure 14 | Full | - | 550 | 900 | ns |
| Output Skew | t_{SKEW1} | $RS = 0V$, ($t_{PHL} - t_{PLH}$), Figure 14 | Full | - | 20 | 65 | ns |
| Output Skew | t_{SKEW2} | $RS = 10k\Omega$, ($t_{PHL} - t_{PLH}$), Figure 14 | Full | - | 60 | 275 | ns |
| Output Skew | t_{SKEW3} | $RS = 50k\Omega$, ($t_{PHL} - t_{PLH}$), Figure 14 | Full | - | 75 | 400 | ns |
| Output Rise Time | t_{r1} | $RS = 0V$, (fast speed - 1Mbps) Figure 14 | Full | 15 | 30 | 85 | ns |
| Output Fall Time | t_{f1} | | Full | 10 | 20 | 65 | ns |
| Output Rise Time | t_{r2} | $RS = 10k\Omega$, (medium speed - 5000kbps) Figure 14 | Full | 125 | 250 | 550 | ns |
| Output Fall Time | t_{f2} | | Full | 100 | 250 | 425 | ns |
| Output Rise Time | t_{r3} | $RS = 50k\Omega$, (slow speed - 250kbps) Figure 14 | Full | 200 | 360 | 800 | ns |
| Output Fall Time | t_{f3} | | Full | 175 | 390 | 600 | ns |
| Total Loop Delay, Driver Input to Receiver Output, Recessive to Dominant | $t_{(LOOP1)}$ | $RS = 0V$, Figure 19 | Full | - | 140 | 225 | ns |
| | | $RS = 10k\Omega$, Figure 19 | Full | - | 380 | 600 | ns |
| | | $RS = 50k\Omega$, Figure 19 | Full | - | 500 | 800 | ns |
| Total Loop Delay, Driver Input to Receiver Output, Dominant to Recessive | $t_{(LOOP2)}$ | $RS = 0V$, Figure 19 | Full | - | 160 | 285 | ns |
| | | $RS = 10k\Omega$, Figure 19 | Full | - | 450 | 700 | ns |
| | | $RS = 50k\Omega$, Figure 19 | Full | - | 575 | 950 | ns |
| Listen to Valid Dominant Time | t_{L-DOM} | Figure 21 | Full | - | 5 | 15 | μs |
| Receiver Switching Characteristics | | | | | | | |

Test Conditions: $V_{CC} = 3V$ to $3.6V$; typical values are at $T_A = +25^\circ C$ (Note 9); unless otherwise specified (Note 7). **Boldface limits apply across the operating temperature range, $-55^\circ C$ to $+125^\circ C$ and over a total ionizing dose of $75krad(Si)$ at $+25^\circ C$ with exposure at a low dose rate of $<10mrads(Si)/s$.** (Continued)

| Parameter | Symbol | Test Conditions | Temp (°C) | Min (Note 8) | Typ (Note 9) | Max (Note 8) | Unit |
|------------------------------------|-------------|-------------------------------------|-----------|----------------------------------------|--------------|----------------------------------------|---------|
| Propagation Delay LOW to HIGH | t_{PLH} | Figure 17 | Full | - | 50 | 110 | ns |
| Propagation Delay HIGH to LOW | t_{PHL} | Figure 17 | Full | - | 50 | 110 | ns |
| Rx Skew | t_{SKEW1} | $ (t_{PHL} - t_{PLH}) $, Figure 17 | Full | - | 2 | 35 | ns |
| Rx Rise Time | t_r | Figure 17 | Full | - | 2 | - | ns |
| Rx Fall Time | t_f | Figure 17 | Full | - | 2 | - | ns |
| VREF/RS Pin Characteristics | | | | | | | |
| VREF Pin Voltage | V_{REF} | $-5\mu A < I_{REF} < 5\mu A$ | Full | $0.45 \times V_{CC}$ | 1.60 | $0.55 \times V_{CC}$ | V |
| | | $-50\mu A < I_{REF} < 50\mu A$ | Full | $0.4 \times V_{CC}$ | 1.6 | $0.6 \times V_{CC}$ | V |
| RS Pin Input Current | $I_{RS(H)}$ | $R_S = 0.75 \times V_{CC}$ | Full | -10.0 | -0.2 | - | μA |
| | $I_{RS(L)}$ | $V_{RS} = 0V$ | Full | -450 | -125 | 0 | μA |

Notes:

- All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified.
- Parameters with MIN and/or MAX limits are 100% tested at $-55^\circ C$, $+25^\circ C$, and $+125^\circ C$, unless otherwise specified.
- Typical values are at $3.3V$. Parameters with a single entry in the "TYP" column apply to $3.3V$. Typical values shown are not guaranteed.
- Parameter included in functional testing.

2.5 Test Circuits and Waveforms

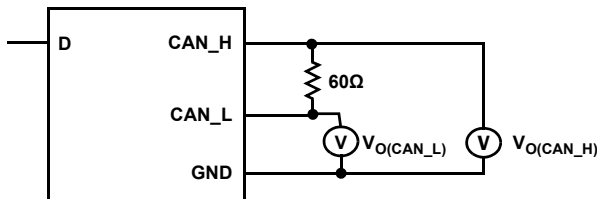


Figure 10. Driver Test Circuit

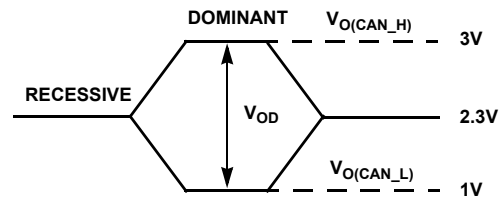


Figure 11. Driver Bus Voltage Definitions

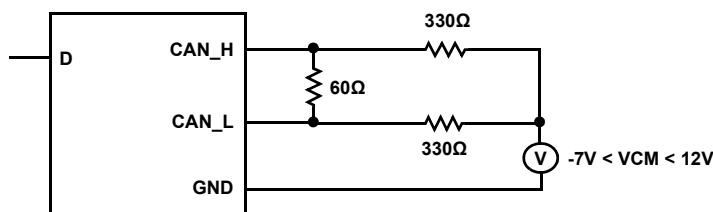
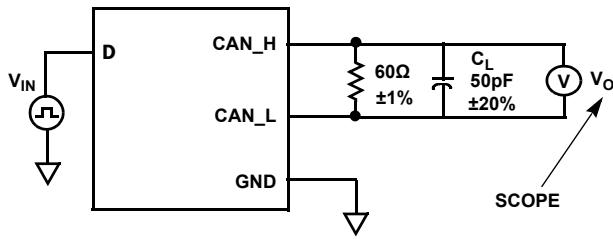


Figure 12. Driver Common-Mode Circuit



$V_{IN} = 125\text{kHz}$, $0\text{V TO } V_{CC}$, DUTY CYCLE 50%, $t_r = t_f \leq 6\text{ns}$, $Z_O = 50\Omega$
 C_L INCLUDES FIXTURE AND INSTRUMENTATION CAPACITANCE

Figure 13. Driver Timing Test Circuit

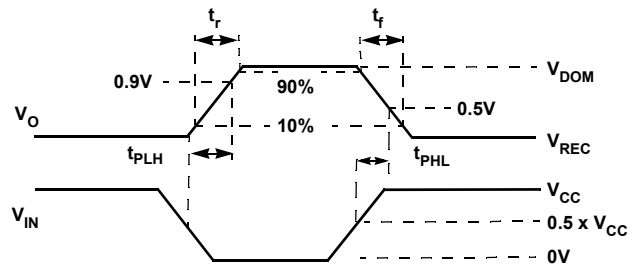


Figure 14. Driver Timing Measurement Points

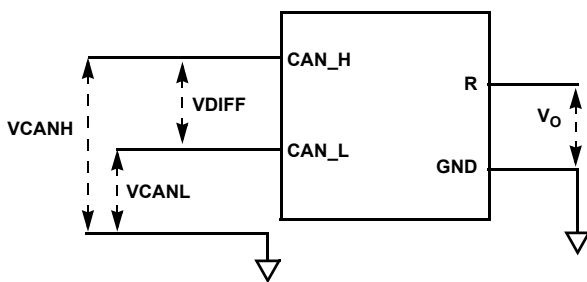
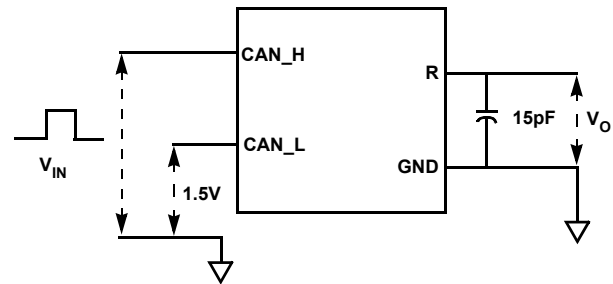


Figure 15. Receiver Voltage Definitions



$V_{IN} = 125\text{kHz}$, DUTY CYCLE 50%, $t_r = t_f = 6\text{ns}$, $Z_O = 50\Omega$
 C_L INCLUDES TEST SETUP CAPACITANCE

Figure 16. Receiver Test Circuit

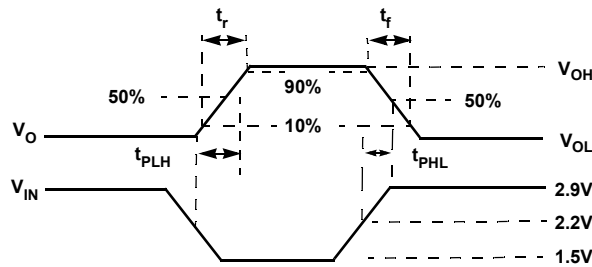


Figure 17. Receiver Test Measurement Points

Table 3. Differential Input Voltage Threshold Test

| INPUT | | OUTPUT | MEASURED |
|--------|--------|--------|----------|
| V_CANH | V_CANL | R | V_DIFF |
| -6.1V | -7V | L | 900mV |
| 12V | 11.1V | L | 900mV |
| -1V | -7V | L | 6V |
| 12V | 6V | L | 6V |
| -6.5V | -7V | H | 500mV |
| 12V | 11.5V | H | 500mV |
| -7V | -1V | H | 6V |
| 6V | 12V | H | 6V |
| Open | Open | H | X |

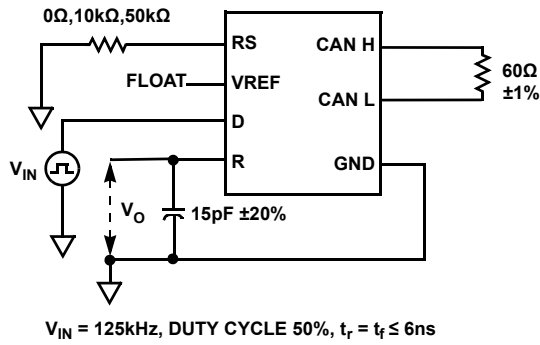


Figure 18. Total Loop Delay Test Circuit

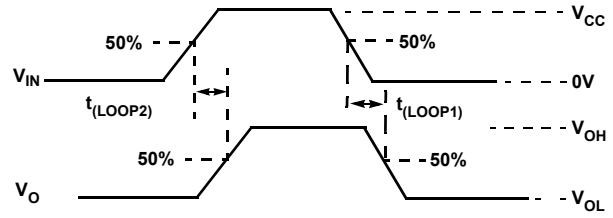


Figure 19. Total Loop Delay Measurement Points

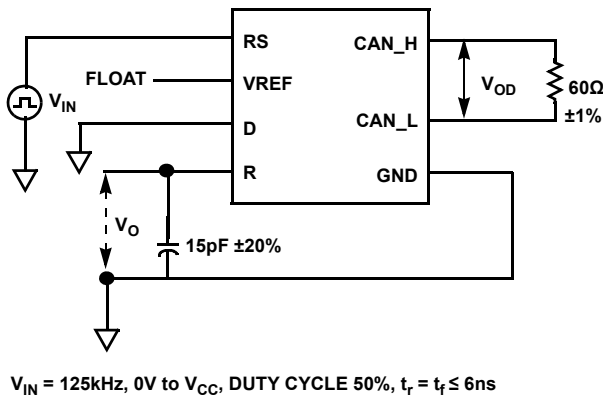


Figure 20. Listen to Valid Dominant Time Circuit

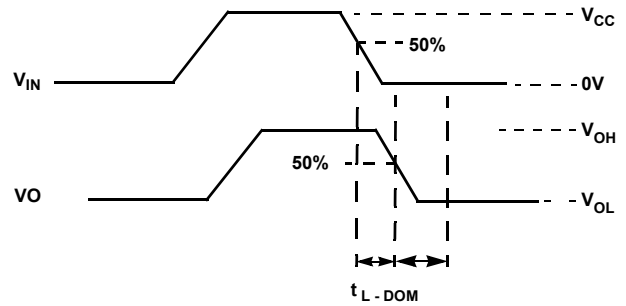


Figure 21. Listen to Valid Dominant Time Measurement Points

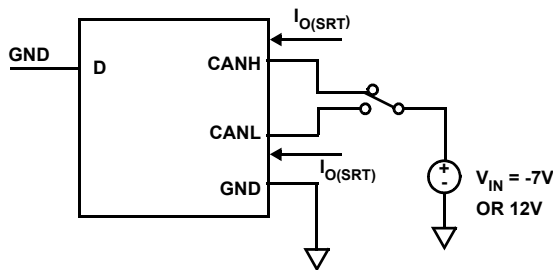


Figure 22. Output Short-Circuit Current Circuit

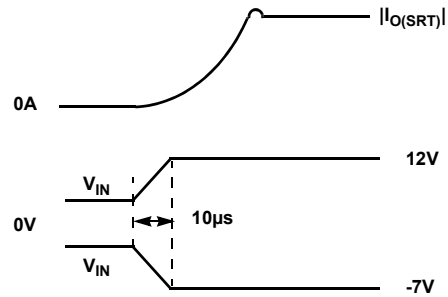


Figure 23. Output Short-Circuit Current Waveforms

3. Typical Performance Curves

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^{\circ}C$; unless otherwise specified.

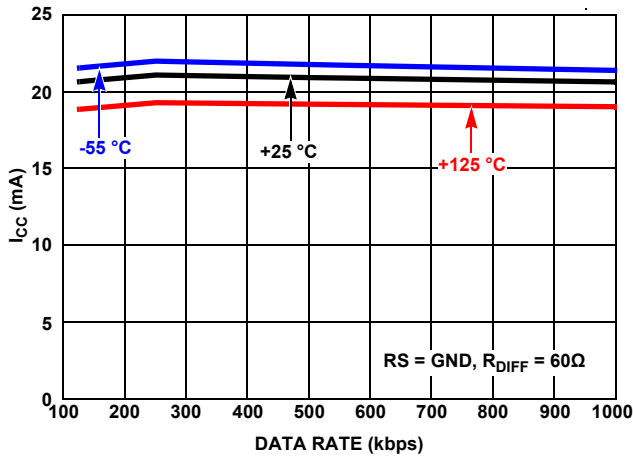


Figure 24. Supply Current vs Fast Data Rate vs Temperature

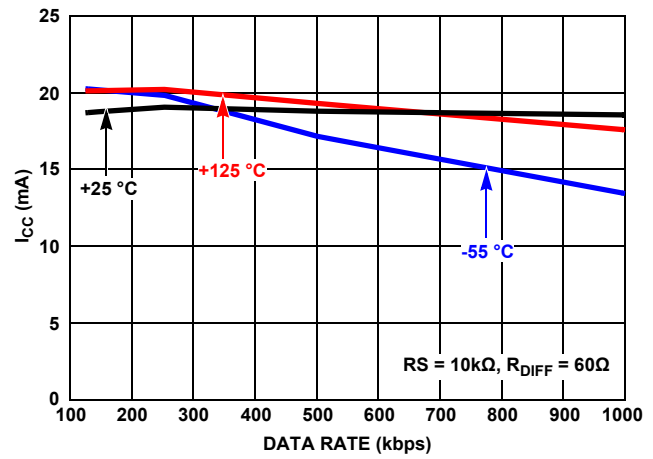


Figure 25. Supply Current vs Medium Data Rate vs Temperature

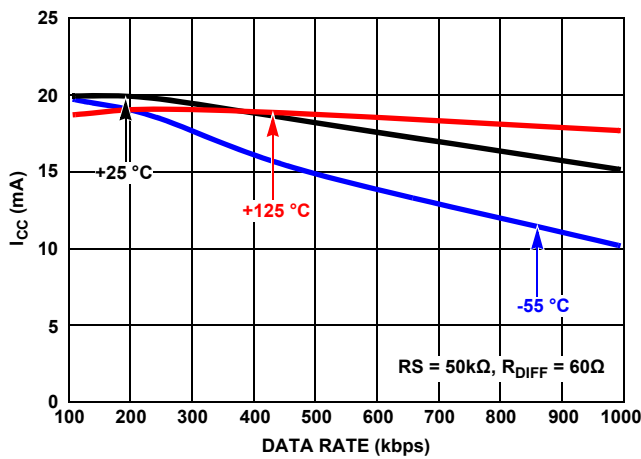


Figure 26. Supply Current vs Slow Data Rate vs Temperature

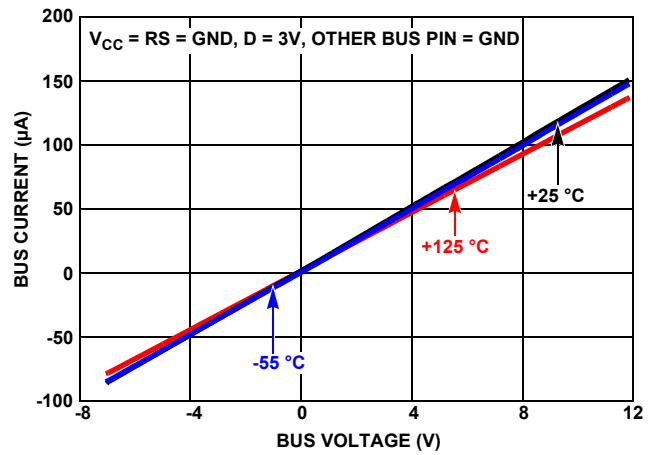


Figure 27. Bus Pin Leakage vs V_{CM} at $V_{CC} = 0V$

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

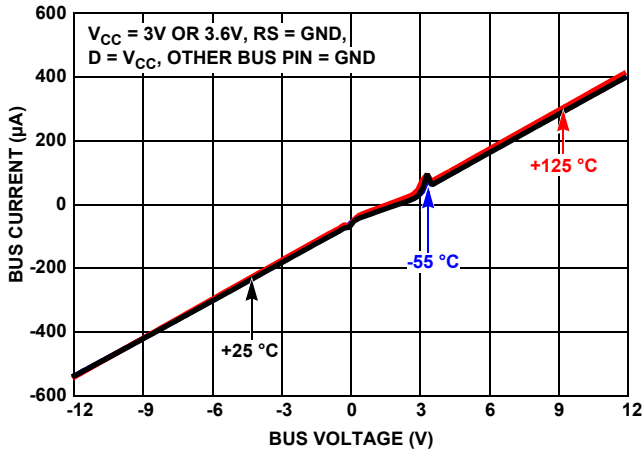


Figure 28. Bus Pin Leakage vs $\pm 12V V_{CM}$

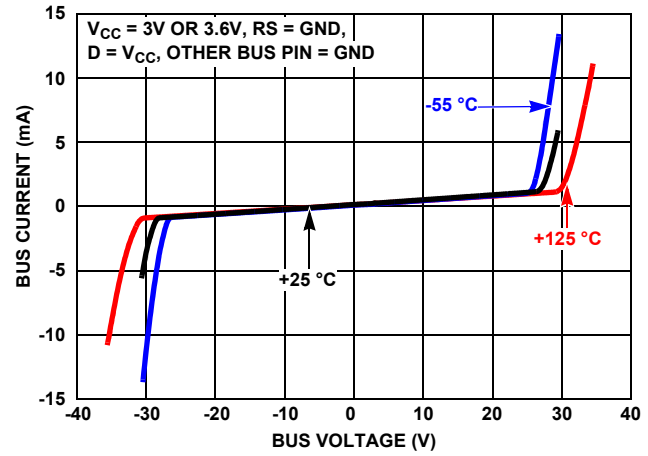


Figure 29. Bus Pin Leakage vs $\pm 35V V_{CM}$

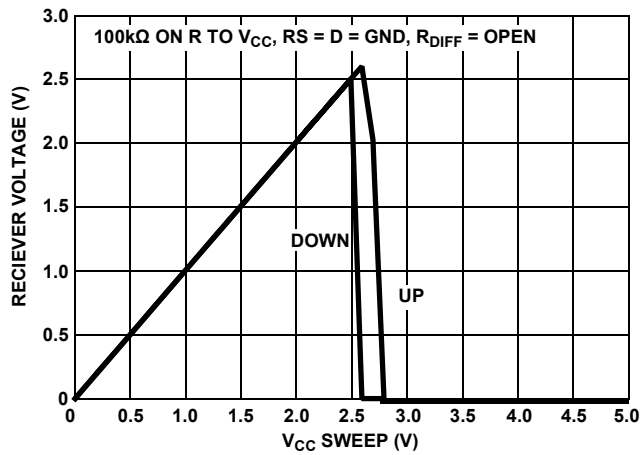


Figure 30. V_{CC} Undervoltage Lockout

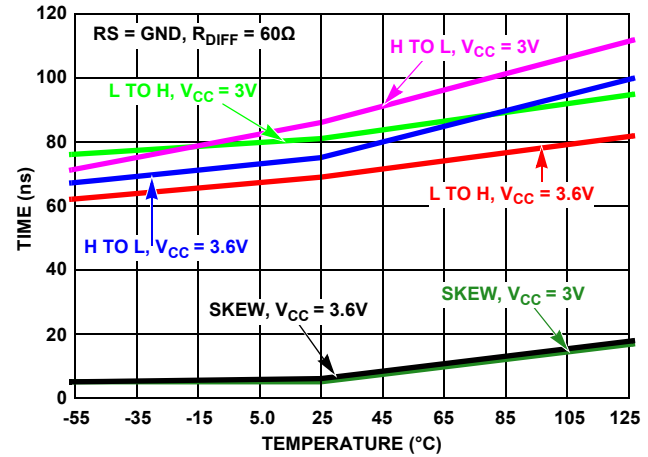


Figure 31. Transmitter Propagation Delay and Skew vs Temperature at Fast Speed

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^{\circ}C$; unless otherwise specified. (Continued)

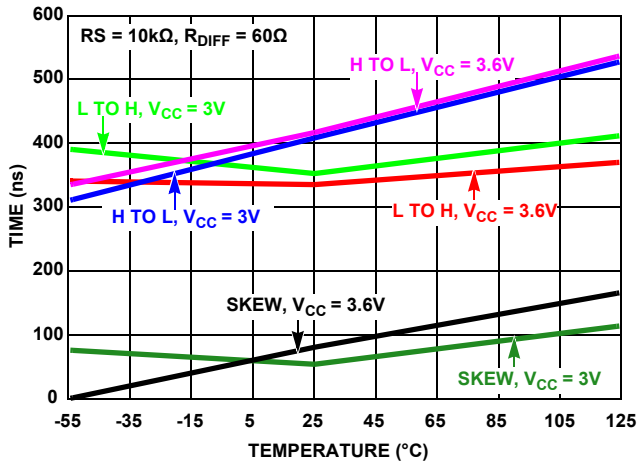


Figure 32. Transmitter Propagation Delay and Skew vs Temperature at Medium Speed

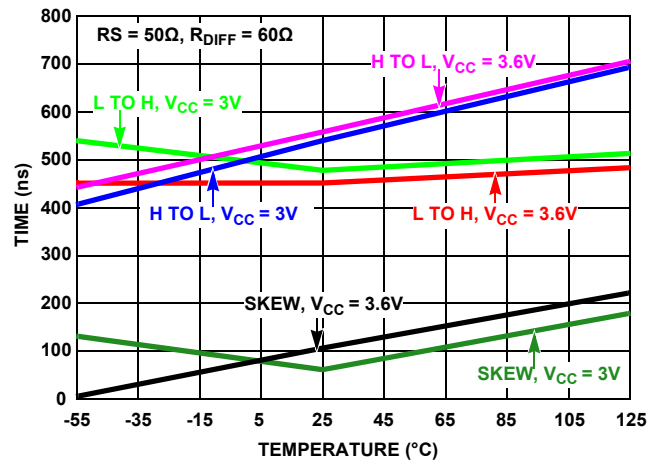


Figure 33. Transmitter Propagation Delay and Skew vs Temperature at Slow Speed

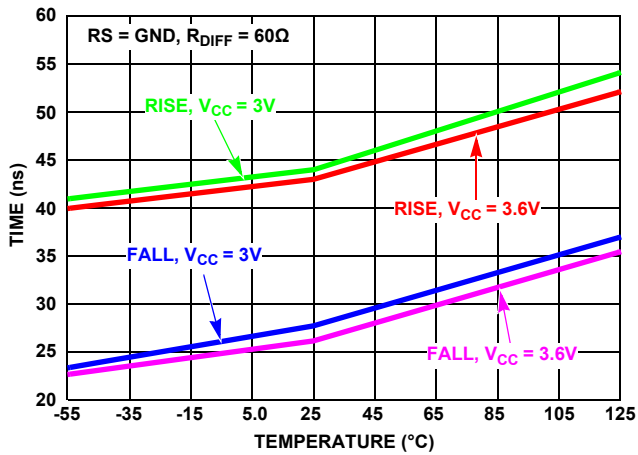


Figure 34. Transmitter Rise and Fall Times vs Temperature at Fast Speed

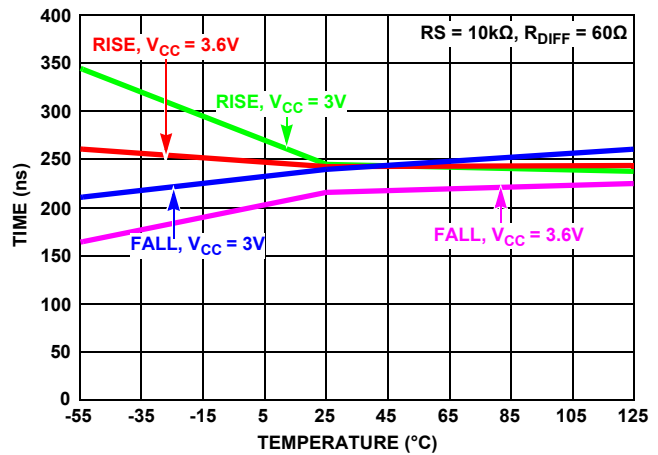


Figure 35. Transmitter Rise and Fall Times vs Temperature at Medium Speed

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

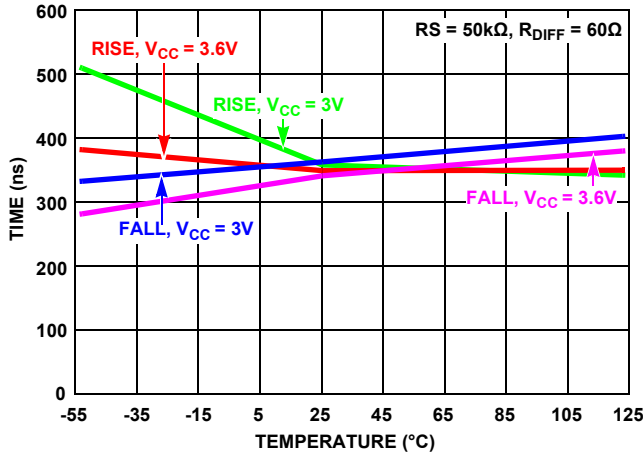


Figure 36. Transmitter Rise and Fall Times vs Temperature at Slow Speed

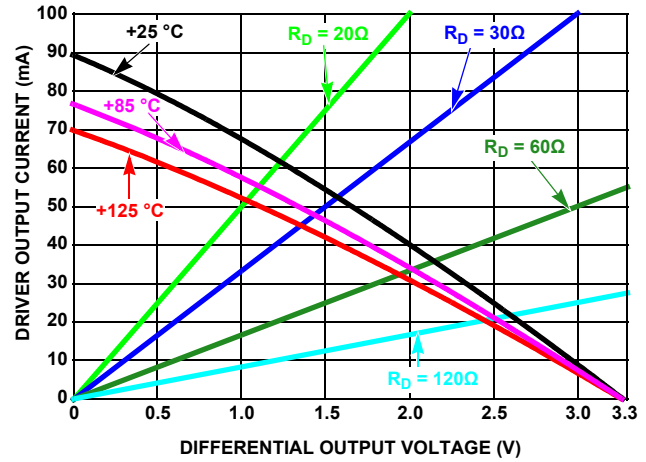


Figure 37. Driver Output Current vs Differential Output Voltage

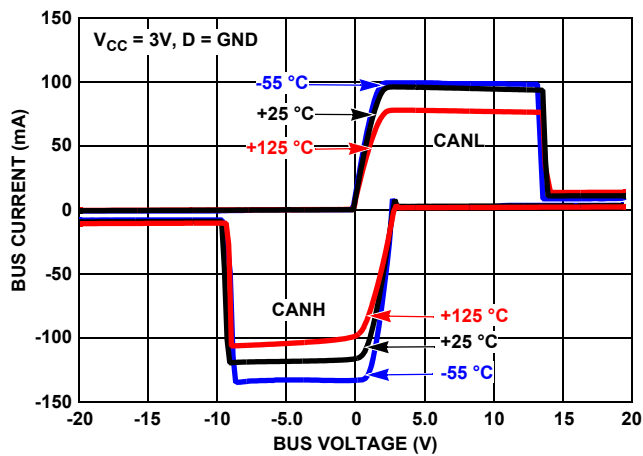


Figure 38. Driver Output Current vs Short-Circuit Voltage vs Temperature

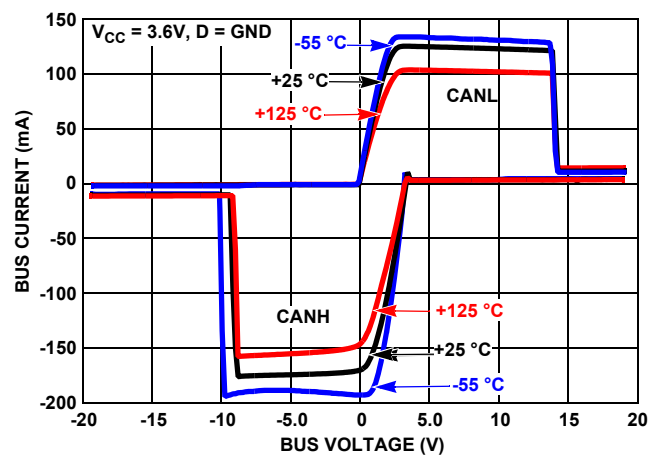


Figure 39. Driver Output Current vs Short-Circuit Voltage vs Temperature

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

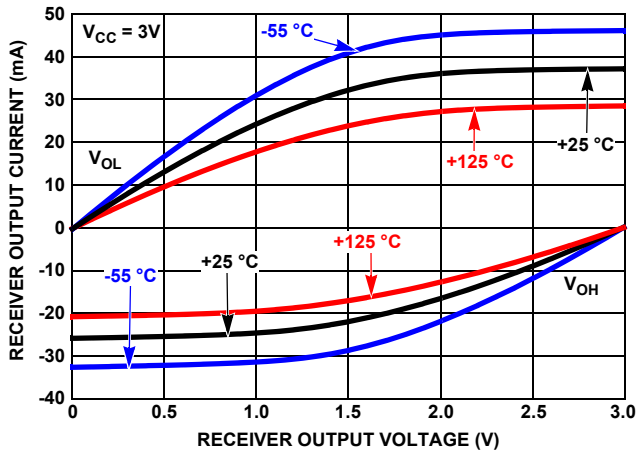


Figure 40. Receiver Output Current vs Receiver Output Voltage at $V_{CC} = 3V$

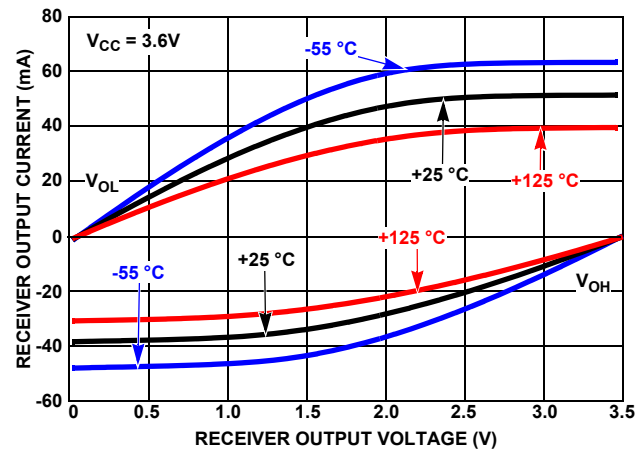


Figure 41. Receiver Output Current vs Receiver Output Voltage at $V_{CC} = 3.6V$

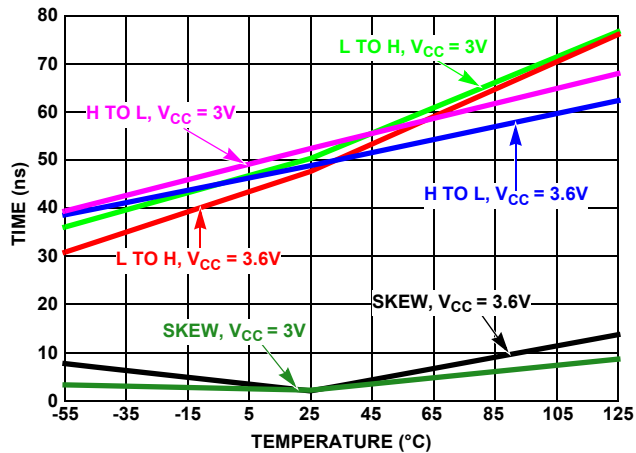


Figure 42. Receiver Propagation Delay and Skew vs Temperature

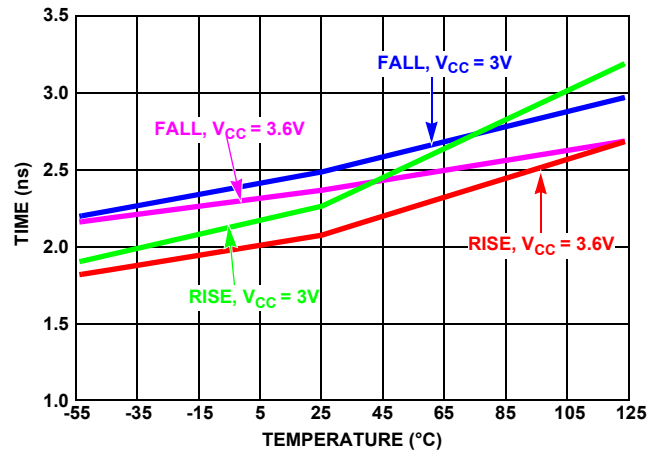


Figure 43. Receiver Rise and Fall Times vs Temperature

$V_{CC} = 3.3V$, $C_L = 15pF$, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

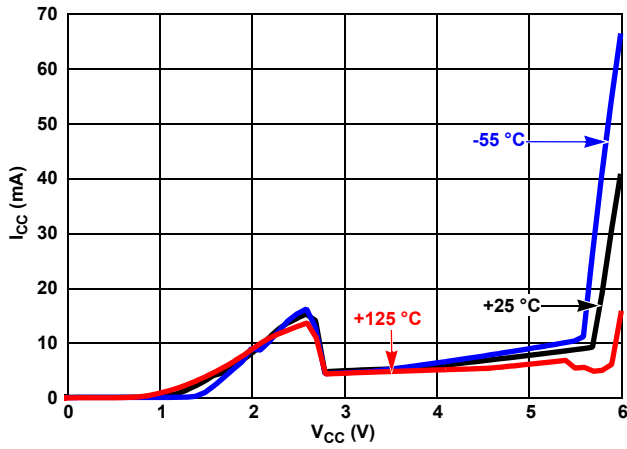


Figure 44. Supply Current vs Supply Voltage vs Temperature

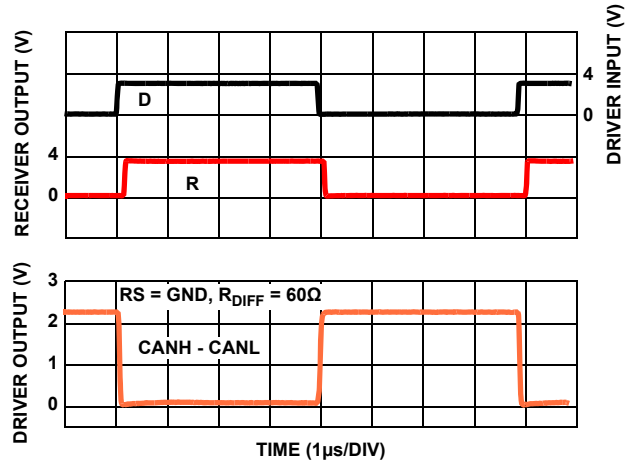


Figure 45. Fast Driver and Receiver Waveforms

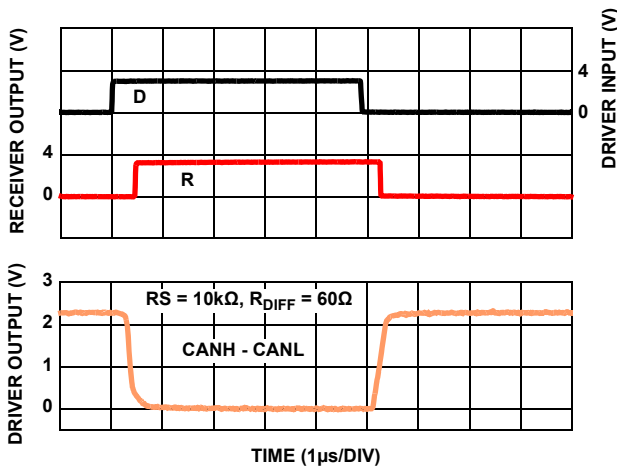


Figure 46. Medium Driver and Receiver Waveforms

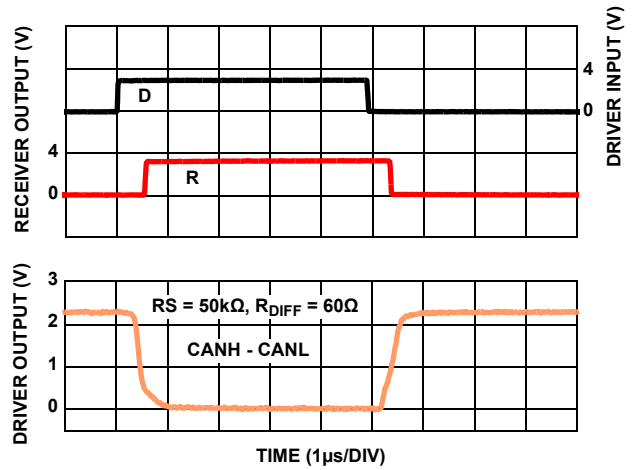


Figure 47. Slow Driver and Receiver Waveforms

4. Functional Description

4.1 Overview

The Intersil ISL72027ASEH is a 3.3V radiation tolerant CAN transceiver that is compatible with the ISO11898-2 standard for use in Controller Area Network (CAN) serial communication systems.

The device performs transmit and receive functions between the CAN controller and the CAN differential bus. It can transmit and receive at bus speeds of to 5Mbps. It is designed to operate across a common-mode range of -7V to +12V, with a maximum of 120 nodes. The device is capable of withstanding $\pm 20V$ on the CANH and CANL bus pins outside of ion beam and $\pm 16V$ under ion beam.

4.2 Slope Adjustment

The transceiver driver has three programmable rise/fall time options programmed by the resistor value connected from the RS pin to GND. A 0Ω resistor sets the part in Fast Speed mode. A resistor of $10k\Omega$ sets the part in Medium Speed mode. A resistor of $50k\Omega$ puts the part in Slow Speed mode. Putting a high logic level on the RS pin places the part in Listen mode. Refer to [“Listen Mode” on page 21](#) for more information.

4.2.1 Fast Speed Mode

Connecting the RS pin directly to GND (0Ω resistor) results in the fastest driver output switching times, limited only by the drive capability of the output state. In Fast Speed mode ($RS = 0V$), the rise/fall times, propagation delays, and total loop delays are optimized for a data rate of 1Mbps.

4.2.2 Medium Speed Mode

In Medium Speed mode ($RS = 10k\Omega$), the rise/fall times, propagation delays, and total loop delays are optimized for a data rate of 500kbps. $RS = 10k\Omega$ provides for a typical slew rate of $12V/\mu s$. The slower edges in Medium Speed mode at 500kbps provide better EMI results than running at 500kbps in Fast Speed mode.

4.2.3 Slow Speed Mode

In Slow Speed mode ($RS = 50k\Omega$), the rise/fall times, propagation delays, and total loop delays are optimized for a data rate of 250kbps. $RS = 50k\Omega$ provides for a typical slew rate of $8V/\mu s$. The slower edges in Slow Speed mode at 250kbps provide better EMI results than running at 250kbps in Medium Speed mode.

4.3 Cable Length

The device can operate according to the ISO11898 specification with a 40m cable and stub length of 0.3m and 60 nodes at 1Mbps. These specifications are greater than the ISO requirement of 30 nodes. The cable type specified is a twisted pair (shielded or unshielded) with a characteristic impedance of 120Ω . Resistors equal to this impedance must be terminated at both ends of the cable. Keep stubs as short as possible to prevent reflections.

4.4 Cold Spare

To reduce the risk of a single-point failure, use redundant bus transceivers in parallel. Space systems call for high reliability in data communications that are resistant to single point failures. This is achieved by using a redundant bus transceiver in parallel. In this arrangement, both active and quiescent devices can be present simultaneously on the bus. The quiescent devices are powered down as cold spares and do not affect the communication of the other active nodes.

The powered down transceiver ($V_{CC} < 200mV$) has a resistance between the VREF pin or the CANH pin or CANL pin to the V_{CC} supply rail of $>480k\Omega$ (maximum) with a typical resistance $>2M\Omega$. The resistance between CANH and CANL of a powered-down transceiver is typically $80k\Omega$. The receiver output (R pin) of a powered-down transceiver ($V_{CC} < 200mV$) is internally connected to ground. Therefore, the receiver outputs of an active transceiver and a cold spare transceiver cannot be connected together in the redundant application.

4.5 Listen Mode

When a high level is applied to the RS pin, the device enters a low power Listen mode. The driver of the transceiver is switched off to conserve power while the receiver remains active. In Listen mode, the transceiver draws 2mA (maximum) of current.

A low level on the RS pin brings the device back to normal operation.

4.6 Using 3.3V Devices in 5V Systems

The differential voltages and recessive common-mode outputs are the same for both the 3.3V and 5V devices. The dominant common-mode output voltage is slightly lower than that of the 5V counterparts. The receiver specifications for both devices are also the same. Although the electrical parameters appear compatible, perform necessary system testing to verify interchangeable operation.

4.7 Split Mode Termination

The VREF pin provides a $V_{CC}/2$ output voltage for Split mode termination. The VREF pin has the same ESD protection, short-circuit protection, and common-mode operating range as the bus pins.

The Split mode termination technique is shown in [Figure 48](#).

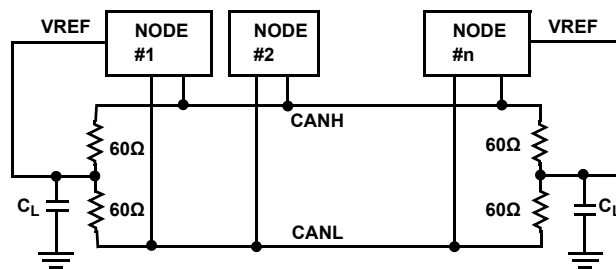


Figure 48. Split Termination

Split mode termination is used to stabilize the bus voltage at $V_{CC}/2$ and prevent it from drifting to a high common-mode voltage during periods of inactivity. The technique improves the electromagnetic compatibility of a network. The Split mode termination is put at each end of the bus.

The C_L capacitor between the two 60Ω resistors filters unwanted high frequency noise to ground. The resistors should have a tolerance of 1% or better and the two resistors should be carefully matched to provide the most effective EMI immunity. A typical value of C_L for a high speed CAN network is 4.7nF, which generates a 3dB point at 1.1Mbps. The capacitance value used is dependent on the signaling rate of the network.

5. Die Characteristics

Table 4. Die and Assembly Related Information

| Die Information | |
|-------------------------------|----------------------------------------------------------------------------------------------------------------------|
| Dimensions | 2413 μ m x 3322 μ m (95 mils x 130.79 mils) Thickness: 305 μ m \pm 25 μ m (12 mils \pm 1 mil) |
| Interface Materials | |
| Glassivation | Type: 12k \AA Silicon Nitride on 3k \AA Oxide |
| Top Metallization | Type: 300 \AA TiN on 2.8 μ m AlCu In Bondpads, TiN has been removed. |
| Backside Finish | Silicon |
| Process | P6SOI |
| Assembly Information | |
| Substrate Potential | Floating |
| Additional Information | |
| Worst Case Current Density | 1.6x10 ⁵ A/cm ² |
| Transistor Count | 4055 |
| Weight of Packaged Device | 0.31 grams |
| Lid Characteristics | Finish: Gold Potential: Grounded, tied to package Pin 2 |

5.1 Metallization Mask Layout

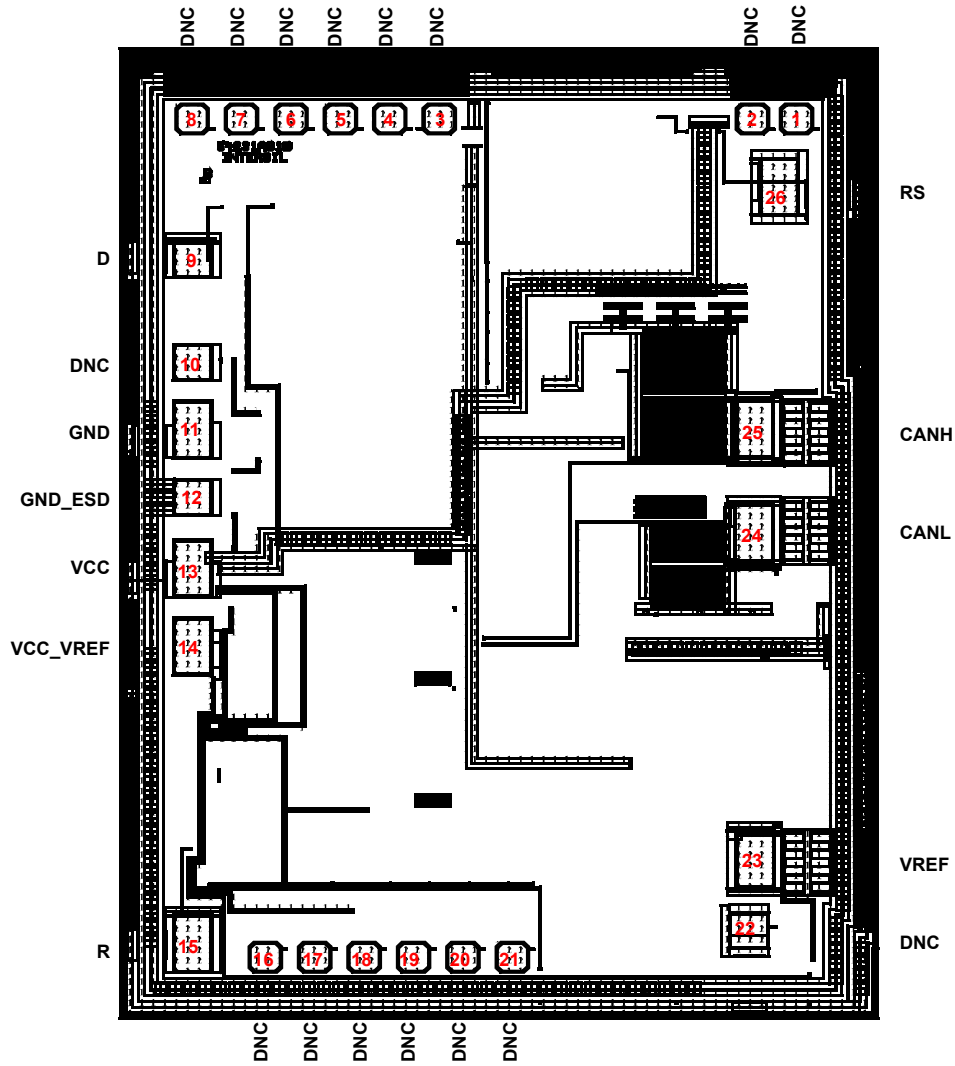


Table 5. ISL72027ASEH Die Layout X-Y Coordinates

| Pad Number | Pad Name | X (μm) | Y (μm) | X | Y |
|------------|----------|---------------------|---------------------|---------|----------|
| 1 | DNC | 90.0 | 90.0 | 901.4 | 1365.6 |
| 2 | DNC | 90.0 | 90.0 | 767.4 | 1365.6 |
| 3 | DNC | 90.0 | 90.0 | -183.23 | 1365.6 |
| 4 | DNC | 90.0 | 90.0 | -333.25 | 1365.6 |
| 5 | DNC | 90.0 | 90.0 | -483.25 | 1365.6 |
| 6 | DNC | 90.0 | 90.0 | -633.25 | 1365.6 |
| 7 | DNC | 90.0 | 90.0 | -783.25 | 1365.6 |
| 8 | DNC | 90.0 | 90.0 | -933.25 | 1365.6 |
| 9 | D | 110.0 | 110.0 | -931.1 | 901.85 |
| 10 | DNC | 110.0 | 110.0 | -931.1 | 563.25 |
| 11 | GND | 110.0 | 180.0 | -931.1 | 342.25 |
| 12 | GND_ESD | 110.0 | 110.05 | -931.1 | 119.42 |
| 13 | VCC | 110.0 | 180.0 | -931.1 | -115.05 |
| 14 | VCC_VREF | 110.0 | 180.05 | -931.1 | -371.08 |
| 15 | R | 110.0 | 180.0 | -931.1 | -1350.0 |
| 16 | DNC | 90.0 | 90.0 | -711.1 | -1394.95 |
| 17 | DNC | 90.0 | 90.0 | -561.1 | -1394.95 |
| 18 | DNC | 90.0 | 90.0 | -411.1 | -1394.95 |
| 19 | DNC | 90.0 | 90.0 | -261.1 | -1394.95 |
| 20 | DNC | 90.0 | 90.0 | -111.1 | -1394.95 |
| 21 | DNC | 90.0 | 90.0 | 38.9 | -1394.95 |
| 22 | DNC | 110.0 | 110.0 | 756.9 | -1307.3 |
| 23 | VREF | 110.0 | 180.0 | 775.3 | -1072.3 |
| 24 | CANL | 110.0 | 180.0 | 772.1 | 2.15 |
| 25 | CANH | 110.0 | 180.05 | 772.1 | 343.33 |
| 26 | RS | 110.0 | 180.0 | 848.1 | 1140.6 |

Note: Origin of coordinates is the center of the die. DNC - Do Not Connect

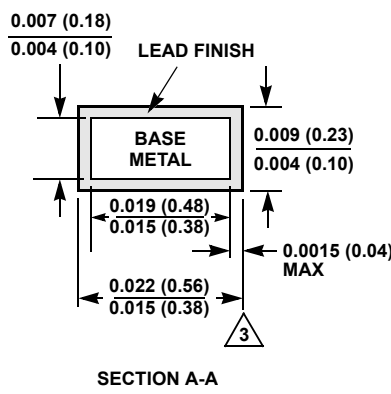
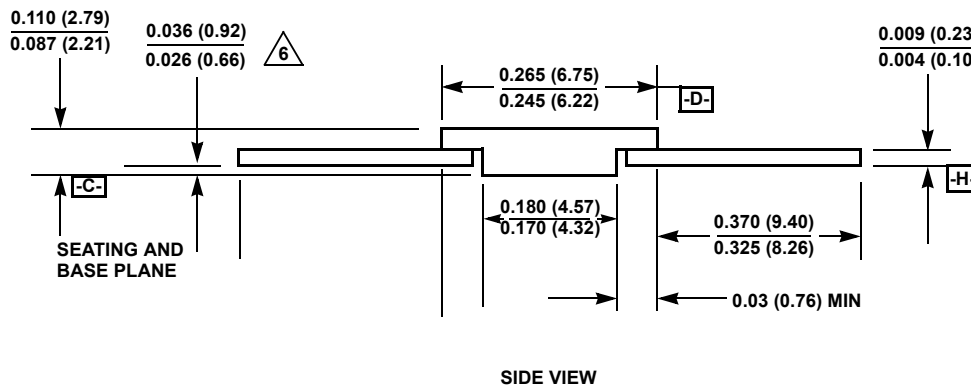
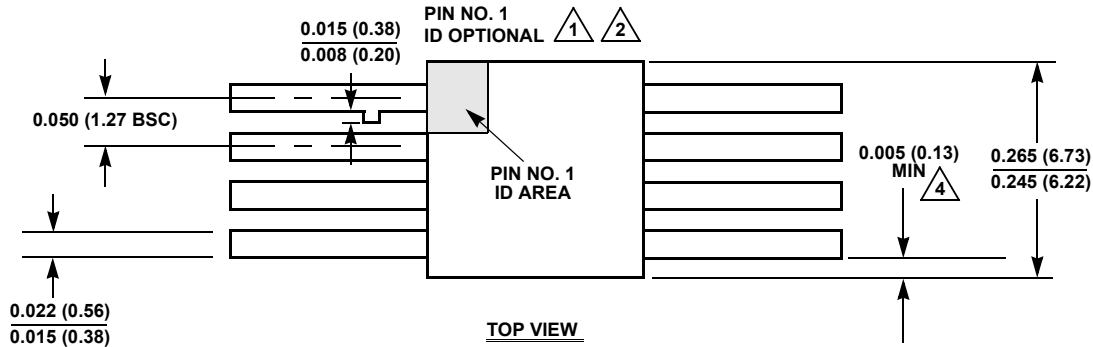
6. Revision History

| Rev. | Date | Description |
|------|--------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| 1.00 | Jul 27, 2017 | Updated Note 5. Updated the maximum limit for Propagation Delay High to Low, t_{PDHL2} from 650ns to 600ns. Updated the maximum limit for Total Loop Delay, Driver Input to Receiver Output, Dominant to Recessive - $t_{(LOOP2)}$ RS = 10kohms from 750ns to 700ns. Updated Slope Adjustment section on page 20. |
| 0.00 | Apr 13, 2017 | Initial release |

7. Package Outline Drawing

For the most recent package outline drawing, see [K8.A](#).

K8.A
 8 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE
 Rev 4, 12/14



NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab may be used to identify pin one.
2. If a pin one identification mark is used in addition to or instead of a tab, the limits of the tab dimension do not apply.
3. The maximum limits of lead dimensions (section A-A) shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
4. Measure dimension at all four corners.
5. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
6. Dimension shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
7. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
8. Controlling dimension: INCH.

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